











SLOS437M - APRIL 2004-REVISED OCTOBER 2016

TL103W Dual Operational Amplifiers With Internal Reference

Features

- Operational Amplifier
 - Low Offset Voltage Max of:
 - TL103WA...3 mV (25°C) and 5 mV (Full Temperature)
 - TL103W...4 mV (25°C) and 5 mV (Full Temperature)
 - Low Supply Current...350 µA/Channel (Typ)
 - Unity Gain Bandwidth...0.9 MHz (Typ)
 - Input Common-Mode Range Includes GND
 - Large Output-Voltage Swing... 0 V to $V_{CC} - 1.5 \text{ V}$
 - Wide Supply-Voltage Range...3 V to 32 V
 - 2.5-kV ESD Protection (HBM)
- Voltage Reference
 - Fixed 2.5-V Reference
 - Tight Tolerance Max of:
 - TL103WA...0.4% (25°C) and 0.8% (Full Temperature)
 - TL103W . . . 0.7% (25°C) and 1.4% (Full Temperature)
 - Low Temperature Drift...7 mV (Typ) Over Operating Temperature Range
 - Wide Sink-Current Range . . . 0.5 mA (Typ) to 100 mA
 - Output Impedance...0.2 Ω (Typ)

2 Applications

- **Battery Chargers**
- Switch-Mode Power Supplies
- Linear Voltage Regulation
- **Data-Acquisition Systems**

3 Description

The TL103W and TL103WA combine the building blocks of a dual operational amplifier and a fixed voltage reference - both of which often are used in the control circuitry of both switch-mode and linear power supplies. OP AMP1 has its noninverting input internally tied to a fixed 2.5-V reference, while OP AMP2 is independent, with both inputs uncommitted.

For the A grade, especially tight voltage regulation can be achieved through low offset voltages for both operational amplifiers (typically 0.5 mV) and tight tolerances for the voltage reference (0.4% at 25°C and 0.8% over operating temperature range).

The TL103W and TL103WA are characterized for operation from -40°C to 105°C.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TL103W TL103WA	SOIC (8)	4.90 mm x 3.91 mm
	WSON (8)	4.00 mm x 4.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Typical Application Circuit

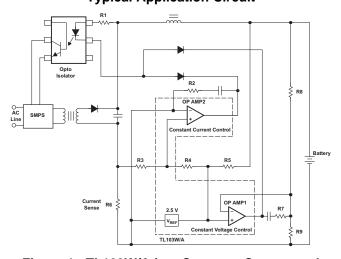


Figure 1. TL103W/A in a Constant-Current and **Constant-Voltage Battery Charger**



T -	I _	-	_ £	^ -	nte	4
19	n	10	ΔT		nto	ntc
10	•	16	OI.	\mathbf{v}	IILE	111.3

1	Features 1	6.6 OP AMP2, Independent Operational Amplifier, Electrical Characteristics6
2	Applications 1	
3	Description 1	6.7 Voltage Reference, Electrical Characteristics 7
4	•	 Total Device, Electrical Characteristics
-	Revision History	7 Device and Documentation Support 8
5	Pin Configuration and Functions 3	7.1 Related Links 8
6	Specifications 4 6.1 Absolute Maximum Ratings 4 6.2 ESD Ratings 4 6.3 Recommended Operating Conditions 4	7.2 Receiving Notification of Documentation Updates 8 7.3 Community Resources
	6.4 Thermal Information4	7.6 Glossary 8
	6.5 OP AMP1, Operational Amplifier With Noninverting Input Connected to the Internal V _{REF} Electrical Characteristics	8 Mechanical, Packaging, and Orderable Information

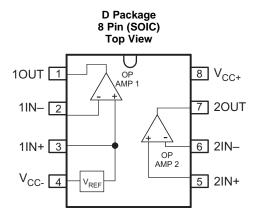
4 Revision History

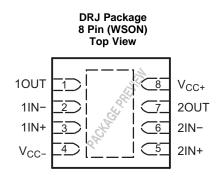
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	and Documentation Support, and Mechanical, Packaging, and Orderable Information sections	
•	Changed positive and negative terminals OP AMP 2 in the D Package image of <i>Pin Configuration and Functions</i>	3
Cł	hanges from Revision K (October 2010) to Revision L	Page
•	, , , , , , , , , , , , , , , , , , , ,	1
•	Changed Features From: 2 kV ESD Protection (HBM) To: 2.5-kV ESD Protection (HBM)	1
•	Changed the Zener diode component to V _{REF} in the <i>Typical Application Circuit</i>	1
•	Changed the Zener diode component to V _{REF} in the D Package of <i>Pin Configuration and Functions</i>	3



5 Pin Configuration and Functions





Pin Functions

	PIN		1/0	DESCRIPTION			
NAME	D	DRJ	1/0	DESCRIPTION			
1OUT	1	1	0	Opamp 1 output			
1IN-	2	2	I	Opamp 1 inverting input			
1IN+	3	3	I	Opamp 1 non-inverting input and Shunt reference cathode terminal			
V _{CC} -	4	4	I	Negative Supply Voltage			
2IN+	5	5	0	Opamp 2 output			
2IN-	6	6	I	Opamp 2 inverting input			
2OUT	7	7	I	Opamp 2 non-inverting input			
V _{CC+}	8	8	I	Positive Supply Voltage			

Product Folder Links: TL103W TL103WA



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage		36	V
V_{ID}	Operational amplifier input differential voltage		36	V
V_{I}	Operational amplifier input voltage range	-0.3	36	V
I _{KA}	Voltage reference cathode current		100	mA
T_{J}	Maximum junction temperature		150	°C
T _{stg}	Storage temperature range	-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{IN}	Supply voltage	3	32	V
I_{K}	Cathode current	1	100	mA
T _A	Operating free-air temperature	-40	105	°C

6.4 Thermal Information

	TL103W / TL103W	
THERMAL METRIC ⁽¹⁾	D (SOIC)	UNIT
	8 PINS	
R _{0JA} Junction-to-ambient thermal resistance	97	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: TL103W TL103WA



6.5 OP AMP1, Operational Amplifier With Noninverting Input Connected to the Internal V_{REF} Electrical Characteristics

 $V_{CC+} = 5 \text{ V}, V_{CC} = \text{GND}, T_A = 25^{\circ}\text{C} \text{ (unless otherwise noted)}$

	PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
		TI 402\\\	V 0.V	25°C		1	4	
V _{IO}	Innut offeet velters	TL103W	V _{icm} = 0 V	Full range			5	m\/
VIO	Input offset voltage	TL103WA	V 0.V	25°C		0.5	3	mV
		ILIUSWA	V _{icm} = 0 V	Full range			5	
αV_{IO}	Input offset-voltage dr	ift		25°C		7		μV/°C
I_{IB}	Input bias current (neg	gative input)		25°C		20		nA
A_{VD}	Large-signal voltage of	ain	$V_{CC+} = 15 \text{ V}, R_L = 2 \text{ k}\Omega, V_{icm} = 0 \text{ V}$	25°C		100		V/mV
k _{SVR}	Supply-voltage rejecti	on ratio	$V_{CC+} = 5 \text{ V to } 30 \text{ V}, V_{icm} = 0 \text{ V}$	25°C	65	100		dB
I _{O(source)}	Output source current		$V_{CC+} = 15 \text{ V}, V_O = 2 \text{ V}, V_{id} = 1 \text{ V}$	25°C	20	40		mA
I _{SC}	Short circuit to GND		V _{CC+} = 15 V	25°C		40	60	mA
	Output sink current		$V_{CC+} = 15 \text{ V}, V_O = 2 \text{ V}, V_{id} = -1 \text{ V}$	25°C	10	12		mA
I _{O(sink)}			$V_{CC+} = 15 \text{ V}, V_O = 0.2 \text{ V}, V_{id} = -1 \text{ V}$	25 0	12	50		μΑ
			$V_{CC} = 30 \text{ V}, R_1 = 2 \text{ k}\Omega$	25°C	26	27		V
V	High-level output volta	000	VCC = 50 V, NL = 2 KΩ	Full range	26			
V _{OH}	r ligit-level output volta	ige	$V_{CC} = 30 \text{ V}, R_L = 10 \text{ k}\Omega$	25°C	27	28		
				Full range	27			
V	Low-level output volta	a o	$R_1 = 10 \text{ k}\Omega$	25°C		5	20	mV
V _{OL}	Low-level output volta	ye 	K_ = 10 K22	Full range			20	IIIV
SR	Slew rate at unity gair	1	$V_{CC+} = 15 \text{ V}, C_L = 100 \text{ pF}, \\ R_L = 2 \text{ k}\Omega, V_I = 0.5 \text{ V} \text{ to 2 V}, \text{ unity gain}$	25°C	0.2	0.4		V/μs
GBW	Gain bandwidth produ	ct	$V_{CC+} = 30 \text{ V}, V_I = 10 \text{ mV}, \\ C_L = 100 \text{ pF}, R_L = 2 \text{ k}\Omega, f = 100 \text{ kHz}$	25°C	0.5	0.9		MHz
THD	Total harmonic distort	ion	$V_{CC+} = 30 \text{ V}, V_O = 2 \text{ V}_{pp}, C_L = 100 \text{ pF}, \\ R_L = 2 \text{ k}\Omega, f = 1 \text{ kHz}, A_V = 20 \text{ dB}$	25°C		0.02%		

Copyright © 2004–2016, Texas Instruments Incorporated



6.6 OP AMP2, Independent Operational Amplifier, Electrical Characteristics

 $V_{CC+} = 5 \text{ V}, V_{CC} = \text{GND}, V_{O} = 1.4 \text{ V}, T_{A} = 25^{\circ}\text{C}$ (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
		TI 100\1		25°C		1	4	
\ <i>/</i>		TL103W	$V_{icm} = 0 V$	Full range			5	\/
V_{IO}	Input offset voltage	TI 400\4/4	V 0V	25°C		0.5	3	mV
		TL103WA	V _{icm} = 0 V	Full range			5	
αV_{IO}	Input offset voltage d	rift		25°C		7		μV/°C
	Input offeet ourrent			25°C		2	75	nA
I _{IO}	Input offset current			Full range			150	IIA
	Innut biog gurrent			25°C		20	150	nA
I _{IB}	Input bias current			Full range			200	IIA
٨	Large-signal voltage	acin	$V_{CC+} = 15 \text{ V}, R_L = 2 \text{ k}\Omega,$	25°C	50	100		V/mV
A _{VD}	Large-signal voltage	gairi	V _O = 1.4 V to 11.4 V	Full range	25			V/IIIV
k _{SVR}	Supply-voltage reject	ion ratio	$V_{CC+} = 5 \text{ V to } 30 \text{ V}$	25°C	65	100		dB
V	Input common-mode	voltago rango	$V_{CC+} = 30 V^{(1)}$	25°C	0		V _{CC+} – 1.5	V
V _{ICR}	input common-mode	voitage range	V _{CC+} = 30 V · ·	Full range	0		V _{CC+} – 2	V
CMRR	Common-mode rejec	tion ratio		25°C	70	85		dB
CIVINN	Common-mode rejec	lion ratio		Full range	60			ub
I _{O(source)}	Output source curren	t	$V_{CC+} = 15 \text{ V}, V_O = 2 \text{ V}, V_{id} = 1 \text{ V}$	25°C	20	40		mA
I _{SC}	Short circuit to GND		V _{CC+} = 15 V	25°C		40	60	mA
	Output sink ourrent		$V_{CC+} = 15 \text{ V}, V_O = 2 \text{ V}, V_{id} = -1 \text{ V}$	25°C	10	12		mA
I _{O(sink)}	Output sink current		$V_{CC+} = 15 \text{ V}, V_O = 0.2 \text{ V}, V_{id} = -1 \text{ V}$	25 C	12	50		μА
			$V_{CC} = 30 \text{ V}, R_L = 2 \text{ k}\Omega$	25°C	26	27		V
V	High-level output volt	200	V _{CC} = 50 V, R _L = 2 KΩ	Full range	26			
V _{OH}	r light-level output voit	age	$V_{CC} = 30 \text{ V}, R_1 = 10 \text{ k}\Omega$	25°C	27	28		V
			V _{CC} = 50 V, K _L = 10 KΩ	Full range	27			
V_{OL}	Low lovel output volt	200	$R_L = 10 \text{ k}\Omega$	25°C		5	20	mV
VOL	Low-level output volta	age	K_ = 10 K22	Full range			20	IIIV
SR	Slew rate at unity gai	n	$ \begin{array}{l} V_{CC+} = 15 \text{ V, } C_L = 100 \text{ pF,} \\ R_L = 2 \text{ k}\Omega, \text{ V}_I = 0.5 \text{ V to } 3 \text{ V,} \\ \text{unity gain} \end{array} $	25°C	0.2	0.4		V/μs
GBW	Gain bandwidth prod	uct	$V_{CC+} = 30 \text{ V}, V_I = 10 \text{ mV}, \\ C_L = 100 \text{ pF}, R_L = 2 \text{ k}\Omega, \\ f = 100 \text{ kHz}$	25°C	0.5	0.9		MHz
THD	Total harmonic distor	tion	$ \begin{array}{c} V_{CC+} = 30 \text{ V, } V_O = 2 \text{ V}_{pp}, \\ C_L = 100 \text{ pF, } R_L = 2 \text{ k}\Omega, \\ f = 1 \text{ kHz, } A_V = 20 \text{ dB} \end{array} $	25°C		0.02%		
V _n	Equivalent input noise	e voltage	V_{CC} = 30 V, R_S = 100 Ω , f = 1 kHz	25°C		50		nV/√ Hz

⁽¹⁾ The input common-mode voltage of either input should not be allowed to go below -0.3 V. The upper end of the common-mode voltage range is $V_{CC+} - 1.5$ V, but either input can go to $V_{CC+} + 0.3$ V (but ≤ 36 V) without damage.

www.ti.com

6.7 Voltage Reference, Electrical Characteristics

		-,						
	PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
		TI 402\\\	1. 10 1	25°C	2.482	2.5	2.518	
.,	Deference veltere	TL103W	$I_K = 10 \text{ mA}$	Full range	2.465		2.535	.,
V_{REF}	Reference voltage	TI 400\\\	10 1	25°C	2.49	2.5	2.51	V
		TL103WA	I _K = 10 mA	Full range	2.48		2.52	
ΔV_{REF}	Reference input voltage deviation over temperature range		$V_{KA} = V_{REF}$, $I_K = 10 \text{ mA}$	Full range		7	30	mV
I _{min}	Minimum cathode current for regulation		V _{KA} = V _{REF}	25°C		0.5	1	mA
z _{ka}	Dynamic impedance	1)	$V_{KA} = V_{REF}$, $\Delta I_K = 1$ mA to 100 mA, $f < 1$ kHz	25°C		0.2	0.5	Ω

$$|z_{ka}| = \frac{\Delta V_{KA}}{\Delta I_{K}}$$

6.8 Total Device, Electrical Characteristics

PARAMETER	TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Total supply current,	V _{CC+} = 5 V, No load	Cull rongs		0.7	1.2	A
excluding cathode-current reference	V _{CC+} = 30 V, No load	Full range			2	mA

Product Folder Links: TL103W TL103WA

⁽¹⁾ The dynamic impedance is defined as



7 Device and Documentation Support

7.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY	
TL103W	Click here	Click here	Click here	Click here	Click here	
TL103WA	Click here	Click here	Click here	Click here	Click here	

7.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

7.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

7.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

7.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

7.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

8 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



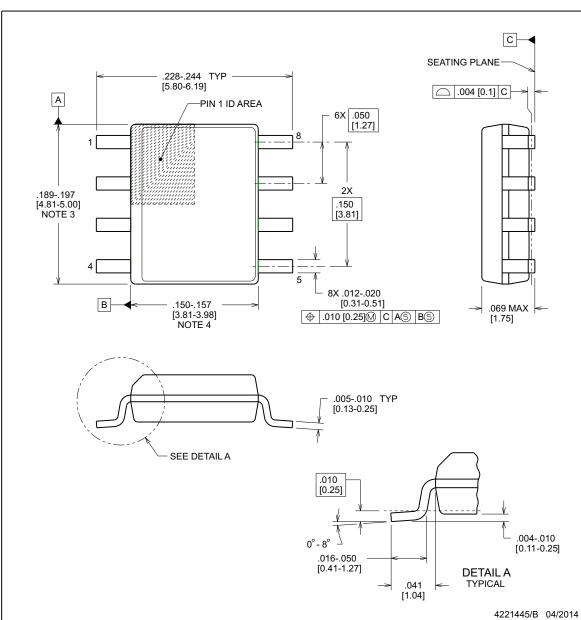
D0008B



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SOIC



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15], per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.

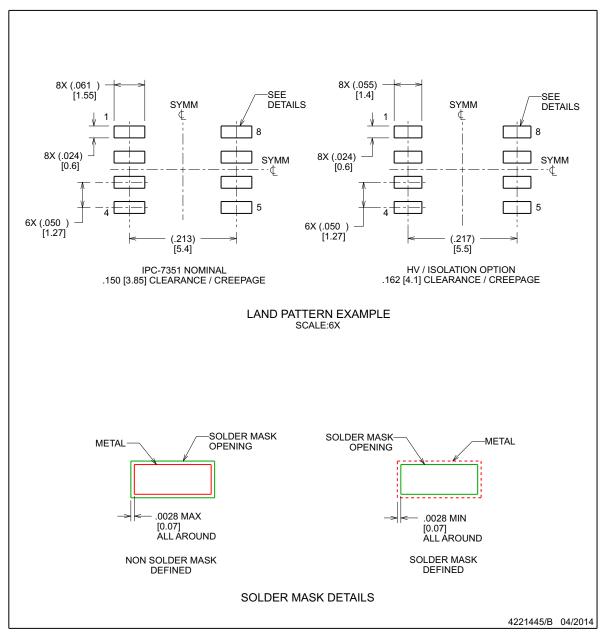
www.ti.com



EXAMPLE BOARD LAYOUT

D0008B

SOIC - 1.75 mm max height



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

www.ti.com

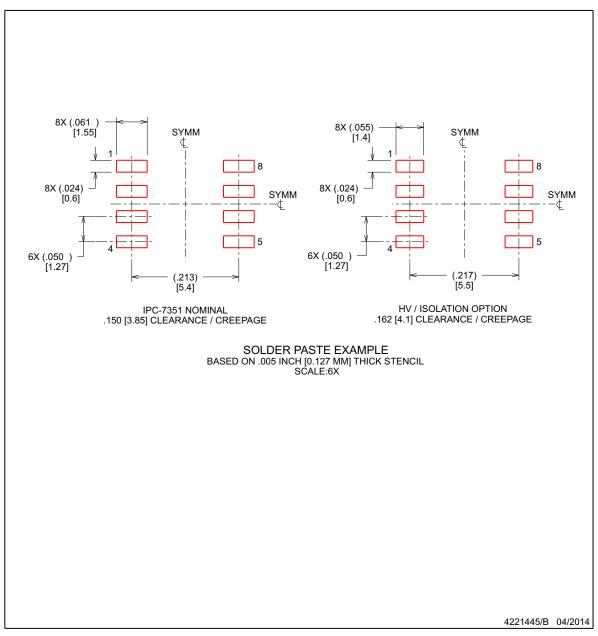


EXAMPLE STENCIL DESIGN

D0008B

SOIC - 1.75 mm max height

OIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

www.ti.com





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TL103WAID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103WA	Samples
TL103WAIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103WA	Samples
TL103WID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	Samples
TL103WIDG4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	Samples
TL103WIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	Samples
TL103WIDRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 105	Z103W	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

10-Dec-2020

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 6-Oct-2016

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

1	7 til dillionolollo alo nominal												
	Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
	TL103WAIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
	TL103WIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 6-Oct-2016



*All dimensions are nominal

Device	Package Type	Package Type Package Drawing I		SPQ	Length (mm)	Width (mm)	Height (mm)	
TL103WAIDR	SOIC	D	8	2500	340.5	338.1	20.6	
TL103WIDR	SOIC	D	8	2500	340.5	338.1	20.6	

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

Tl's products are provided subject to Tl's Terms of Sale (www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such Tl products. Tl's provision of these resources does not expand or otherwise alter Tl's applicable warranties or warranty disclaimers for Tl products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2020, Texas Instruments Incorporated